SN74CBTLV1G125 Low-Voltage Single FET Bus Switch

1 Features

- 5Ω switch connection between two ports
- Rail-to-rail switching on data I/O ports
- I_{off} supports partial-power-down mode operation

2 Applications

- Datacenter and enterprise computing
- Broadband fixed line access
- Building automation
- Wired networking
- Motor drives

3 Description

The SN74CBTLV1G125 device features a single high-speed line switch. The switch is disabled when the output-enable ($\overline{OE}$) input is high.

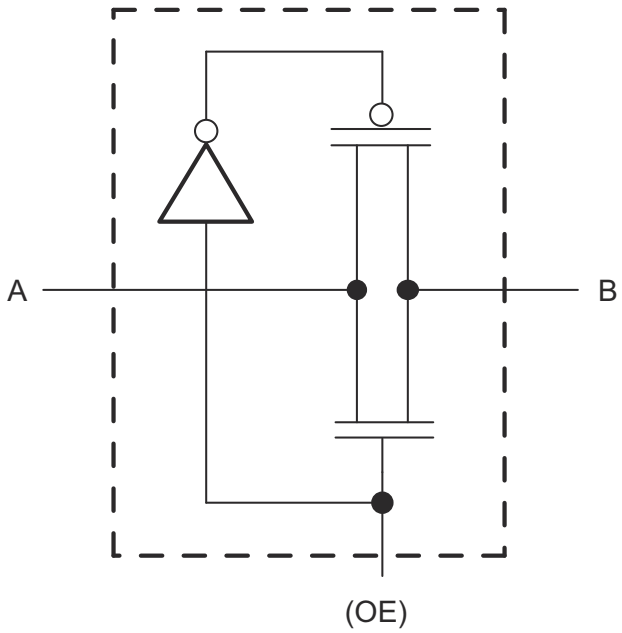
This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ must be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Package Information

PART NUMBER	PACKAGE(1)	BODY SIZE
SN74CBTLV1G125	SC70 (5)	2.00mm × 1.25mm
	SOT-23 (5)	2.90mm × 1.60mm

(1) For all available packages, see Section 11.



Simplified Schematic, Each FET Switch

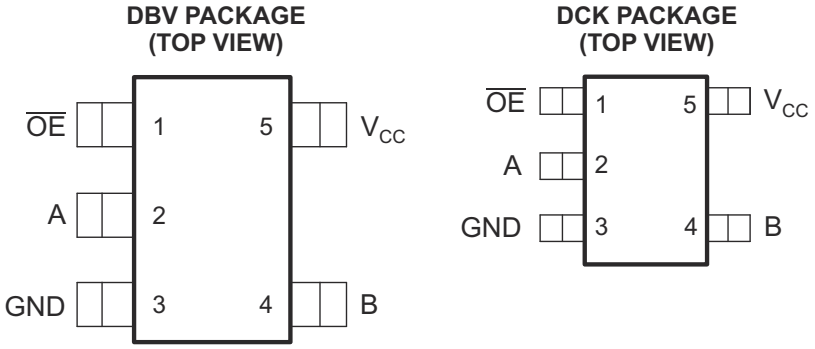
An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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4 Pin Configuration and Functions



See mechanical drawings for dimensions.

Figure 4-1. DBV 5-Pin SOT-23 and DCK 5-Pin SC70 (Top View)

Table 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
$\overline{OE}$	1	I	Active low enable
A	2	I/O	Switch I/O
GND	3	-	Ground
B	4	I/O	Switch I/O
V_{CC}	5	-	Power Supply

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5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	4.6	V
V_I	Input voltage range(2)		–0.5	4.6	V
	Continuous channel current			128	mA
I_{IK}	Input clamp current	$V_{I/O} < 0$		–50	mA
T_{stg}	Storage temperature range		–65	150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level control input voltage	V_{CC} = 2.3V to 2.7V	1.7		V
		V_{CC} = 2.7V to 3.6V	2		
V_{IL}	Low-level control input voltage	V_{CC} = 2.3V to 2.7V		0.7	V
		V_{CC} = 2.7V to 3.6V		0.8	
T_A	Operating free-air temperature		–40	85	°C

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See the TI application note, *Implications of Slow or Floating CMOS Inputs*.

5.4 Thermal Information

THERMAL METRIC(1)		SN74CBTLV1G125		UNIT
		SC70 (DCK)	SOT-23 (DBV)	
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	276.9	249.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	179.1	174.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	183.6	83.9	°C/W
ψ_{JT}	Junction-to-top characterization parameter	114.7	67.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	182.7	83.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application note.

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5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP(1)	MAX	UNIT
V_{IK}		V_{CC} = 3V, I_I = –18mA					–1.2	V
I_I		V_{CC} = 3.6V, V_I = V_{CC} or GND					±1	µA
I_{off}		V_{CC} = 0, V_I or V_O = 0 to 3.6V					10	µA
I_{CC}		V_{CC} = 3.6V, I_O = 0, V_I = V_{CC} or GND					10	µA
ΔI_{CC}(2)	Control inputs	V_{CC} = 3.6V, One input at 3V, Other inputs at V_{CC} or GND					300	µA
C_i	Control inputs	V_I = 3V or 0				2.5		pF
$C_{io(OFF)}$		V_O = 3V or 0, $\overline{OE}$ = V_{CC}				7		pF
r_{on}(3)		V_{CC} = 2.3V, TYP at V_{CC} = 2.5V	V_I = 0	I_I = 64mA		7	10	Ω
				I_I = 24mA		7	10	
			V_I = 1.7V,	I_I = 15mA		15	25	
		V_{CC} = 3V	V_I = 0	I_I = 64mA		5	7	
				I_I = 24mA		5	7	
			V_I = 2.4V,	I_I = 15mA		10	15	

(1) All typical values are at V_{CC} = 3.3V (unless otherwise noted), T_A = 25°C.
(2) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(3) Measured by the voltage drop between A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

5.6 Switching Characteristics

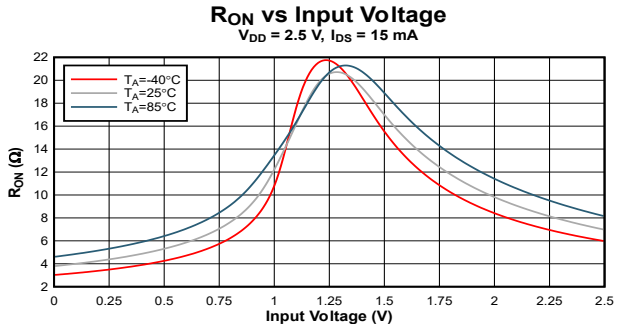
over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

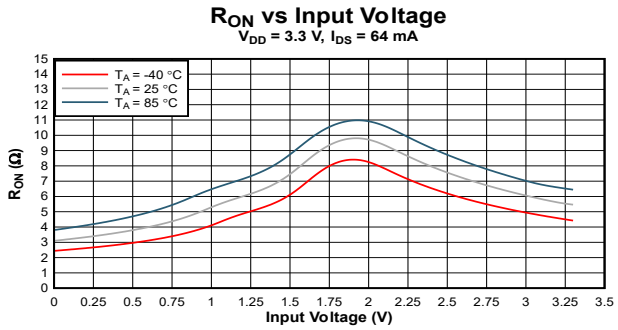
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5V ± 0.2V		V_{CC} = 3.3V ± 0.3V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}(1)	A or B	B or A		0.15		0.25	ns
t_{en}	$\overline{OE}$	A or B	1	4	1	4	ns
t_{dis}	$\overline{OE}$	A or B	1	5	1	4.1	ns

(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance of 50pF, when driven by an appropriate voltage source (zero output impedance).

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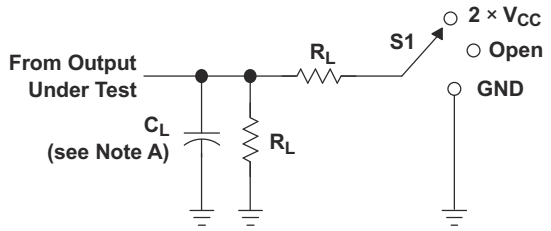
5.7 Typical Characteristics





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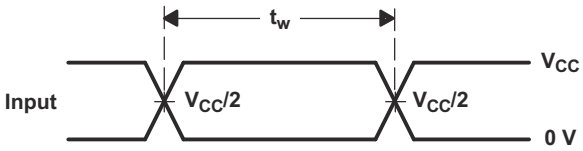
6 Parameter Measurement Information



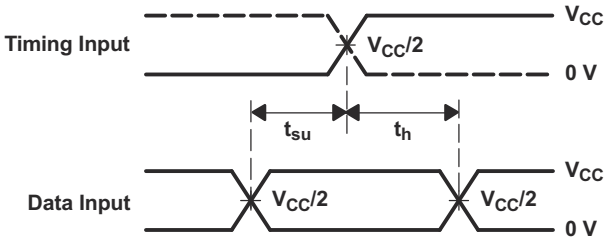
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

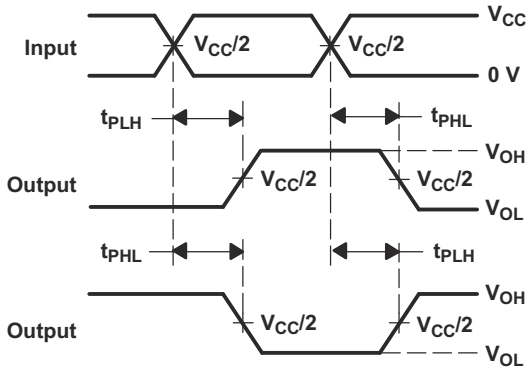
V_{CC}	C_L	R_L	V_D
2.5 V ±0.2 V	30 pF	500 Ω	0.15 V
3.3 V ±0.3 V	50 pF	500 Ω	0.3 V



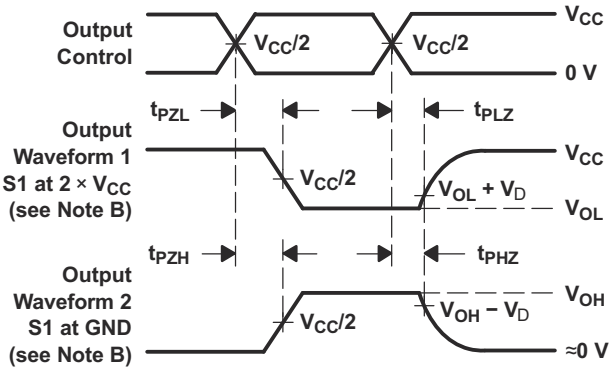
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10MHz, Z_O = 50Ω, t_r ≤ 2ns, t_f ≤ 2ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

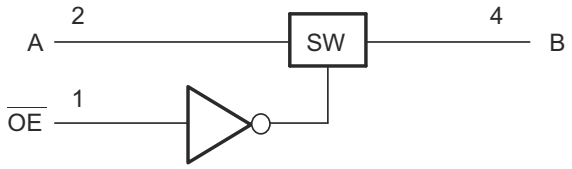
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7 Detailed Description

7.1 Overview

The SN74CBTLV1G125 device is a 1-channel 1:1 high-speed FET switch. The low ON-state resistance of the switch allows connections to be made with minimal propagation delay. The ($\overline{OE}$) pin is an active low logic control pin that controls the data flow. The FET is disabled when the output-enable ($\overline{OE}$) input is high. This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off. To ensure the high-impedance state during power up or power down, OE should be tied to VCC through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

7.2 Functional Block Diagram



7.3 Feature Description

The SN74CBTLV1G125 features 5Ω switch connection between ports, allowing for low signal loss across the switch. Rail-to-rail switching on data I/O allows for full voltage swing outputs. I_{off} supports partial-power-down mode operation, protecting the chip from voltages at output ports when it is not powered on.

7.4 Device Functional Modes

Table 7-1. Function Table

INPUT $\overline{OE}$	FUNCTION
L	A port = B port
H	Disconnect

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8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74CBTLV1G125 can be used to switch a signal path. The switch is bidirectional, so the A and B pins can be used as either inputs or outputs. This switch is typically used when there is one signal path that needs to be isolated at certain times.

8.2 Typical Application

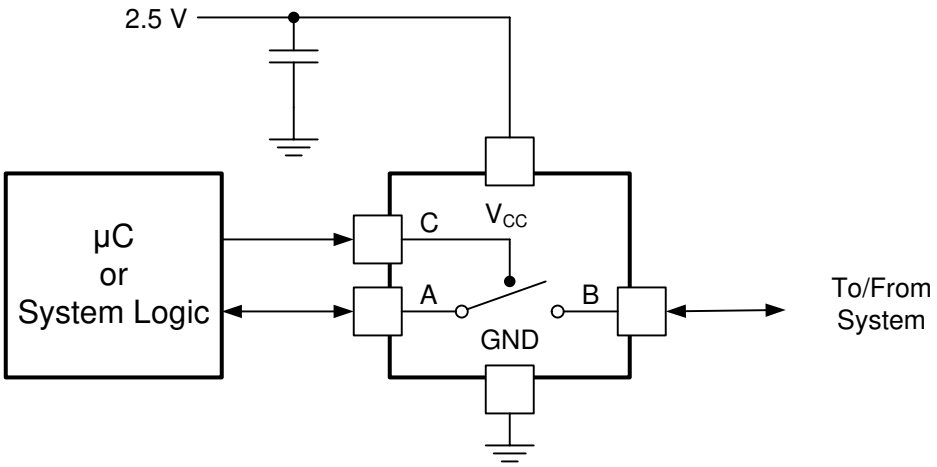


Figure 8-1. Typical Application

8.2.1 Design Requirements

The SN74CBTLV1G125 device can be properly operated without any external components. TI recommends pulling up the digital control pin (OE) to VCC or pulling down to GND to avoid undesired switch positions that could result from the floating pin. A floating digital pin could cause excess current consumption refer to .

8.2.2 Detailed Design Procedure

When $\overline{OE}$ is high, the active bus. This means that there is a low impedance path between the A and B pins. The 0.1µF capacitor on VCC is a decoupling capacitor and must be placed as close as possible to the device.

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the Recommended Operating Conditions table. Each VCC terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1µF bypass capacitor is recommended. If multiple pins are labeled VCC, then a 0.01µF or 0.022µF capacitor is recommended for each VCC because the VCC pins are tied together internally. For devices with dual supply pins operating at different voltages, for example VCC and VDD, a 0.1µF bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1µF and 1µF are commonly used in parallel. The bypass capacitor must be installed as close to the power terminal as possible for best results.

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8.4 Layout

8.4.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight, and therefore; some traces must turn corners. Figure 8-2 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

8.4.2 Layout Example

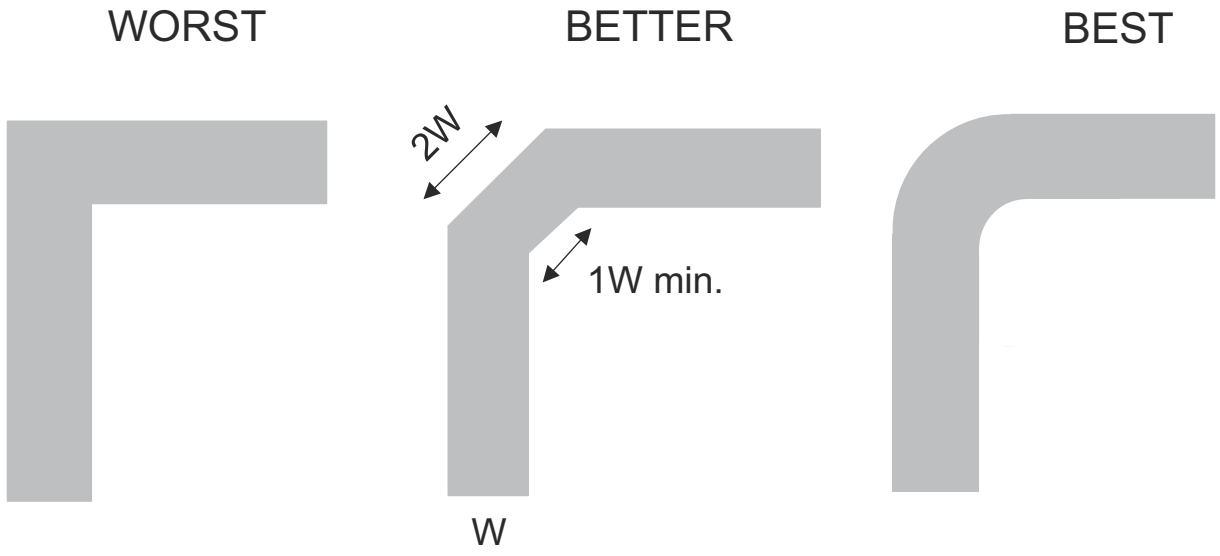


Figure 8-2. Example Layout

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9 Device and Documentation Support

9.1 Device Support

9.2 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.3 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

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9.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision H (June 2006) to Revision I (November 2026)	Page
• Added the *Application*, *Pin Configuration and Functions*, *Device Functional Modes*, *Device and Documentation Support*, and *Mechanical, Packaging, and Orderable Information* sections	1
• Removed Ordering Information table	1
• Updated the numbering format for tables, figures, and cross-references throughout the document	1
• Updated continuous channel current from: *128V* to *128mA* in *Absolute Maximum Ratings*	4
• Removed package thermal impedance from *Absolute Maximum Ratings*	4
• Updated Thermal Information	4
• Added Typical Characteristics	6

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74CBTLV1G125DBVRG4	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(V25K, V25R)
74CBTLV1G125DBVRG4.B	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(V25K, V25R)
SN74CBTLV1G125DBVR	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(V25J, V25K, V25R)
SN74CBTLV1G125DBVR.A	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(V25J, V25K, V25R)
SN74CBTLV1G125DBVR.B	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(V25J, V25K, V25R)
SN74CBTLV1G125DCKR	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(VM5, VMJ, VMO, VMR)
SN74CBTLV1G125DCKR.A	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(VM5, VMJ, VMO, VMR)
SN74CBTLV1G125DCKR.B	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(VM5, VMJ, VMO, VMR)

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74CBTLV1G125 :

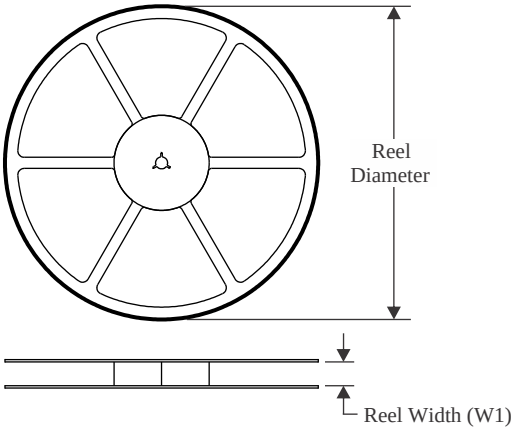
- Automotive : SN74CBTLV1G125-Q1

NOTE: Qualified Version Definitions:

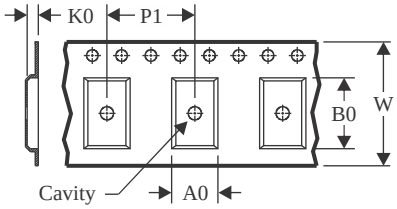
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

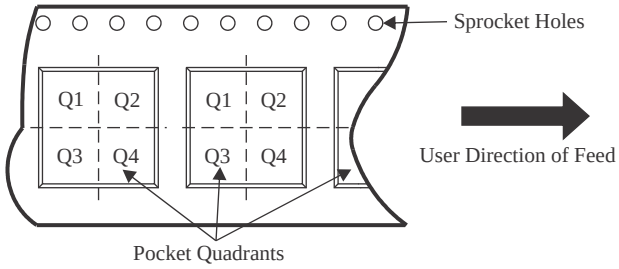


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

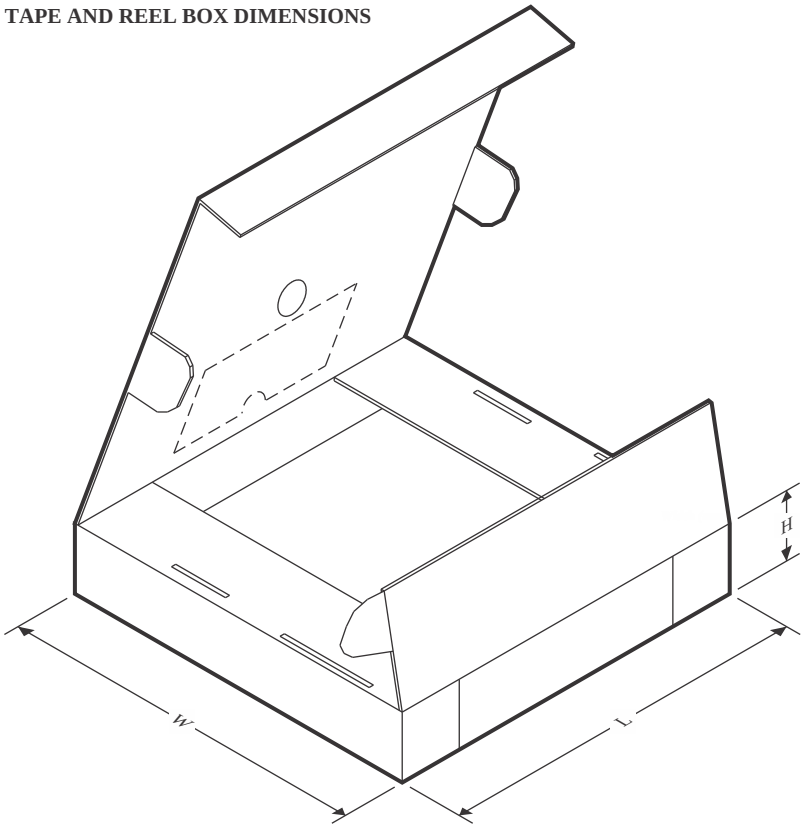
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74CBTLV1G125DBVRG4	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

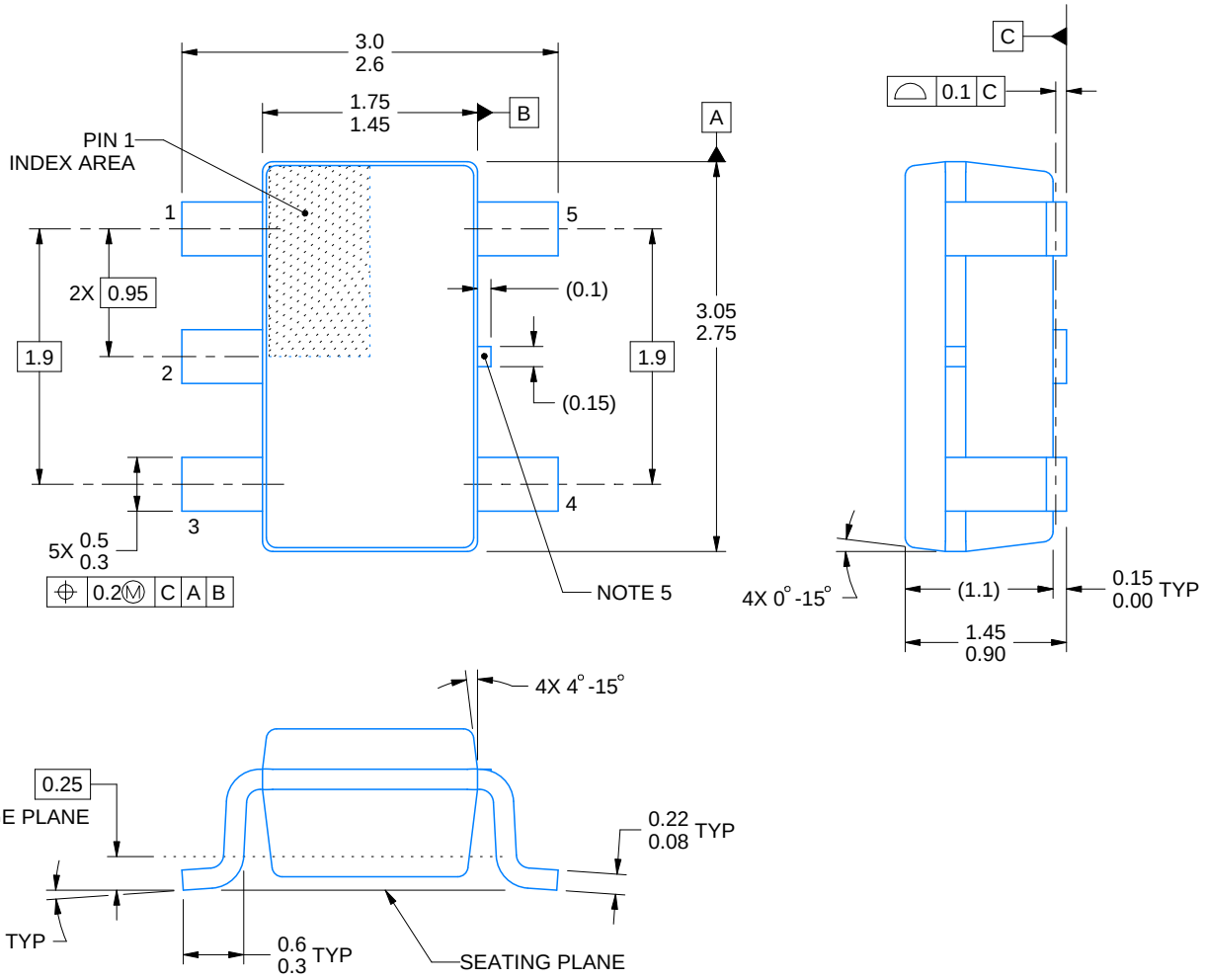
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74CBTLV1G125DBVRG4	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	208.0	191.0	35.0
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74CBTLV1G125DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	203.0	203.0	35.0
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74CBTLV1G125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0

PACKAGE OUTLINE

DBV0005A

SOT-23 - 1.45 mm max height

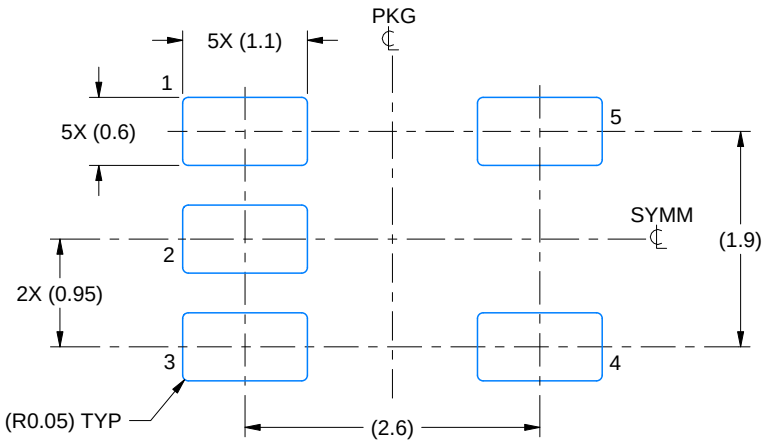
SMALL OUTLINE TRANSISTOR



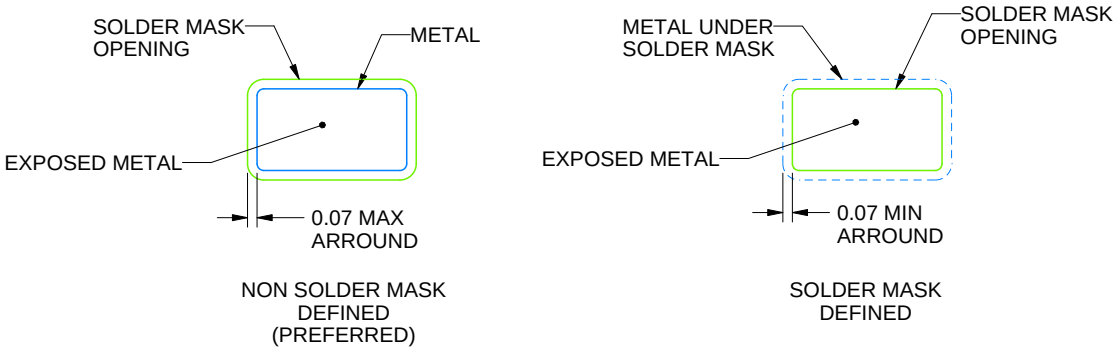
4214839/K 08/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

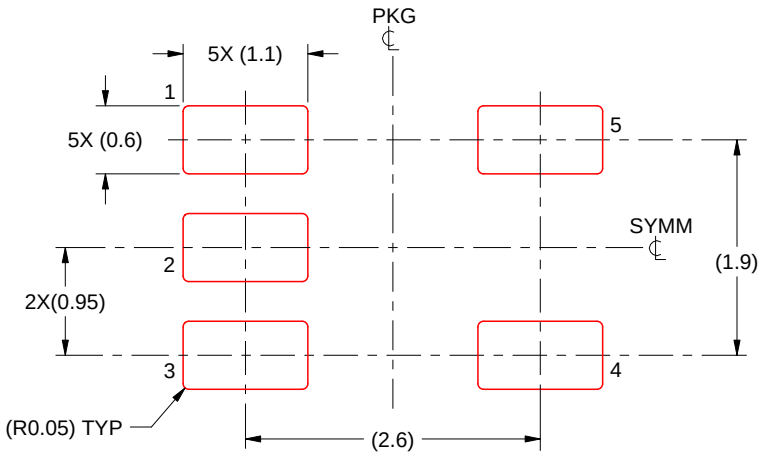


SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

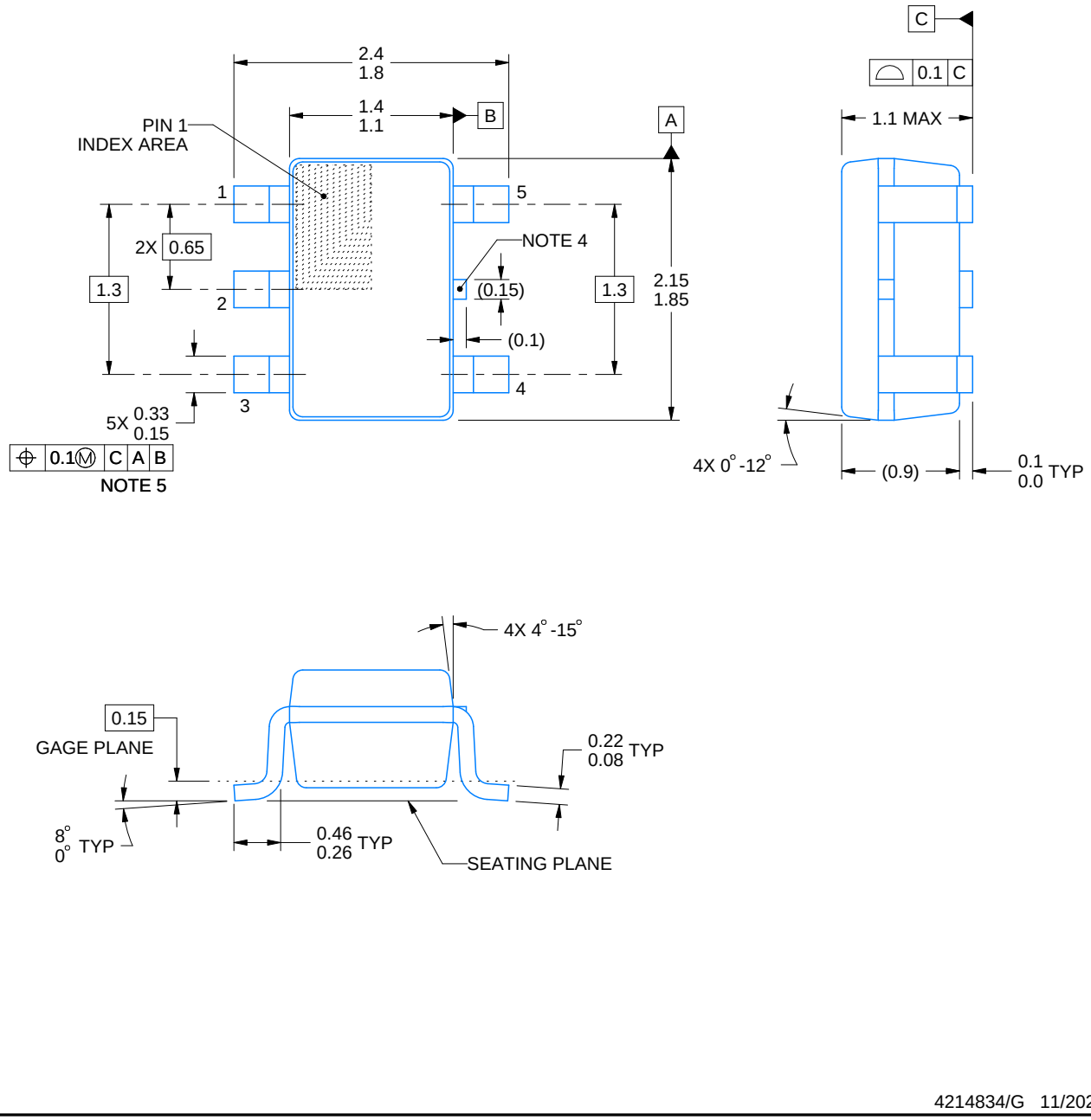
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

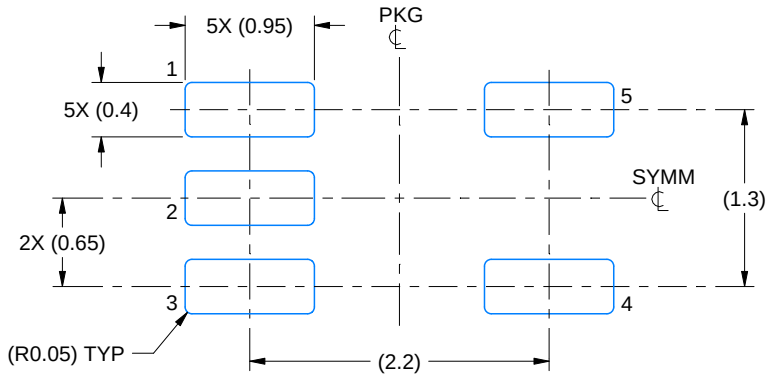
SMALL OUTLINE TRANSISTOR



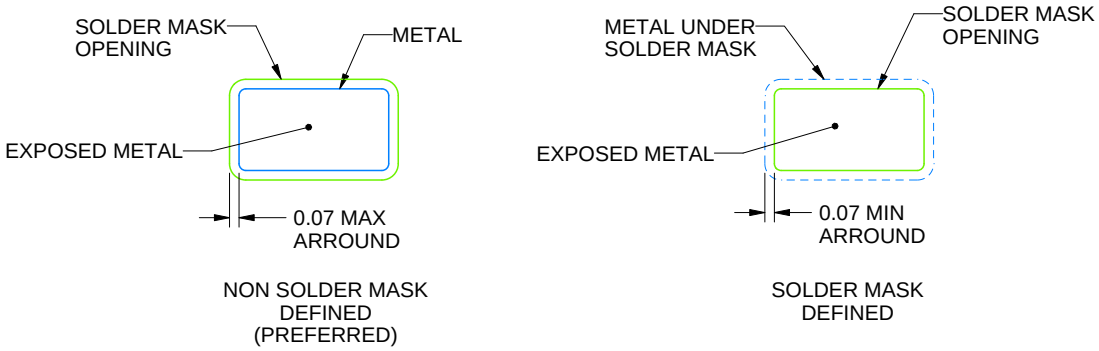
4214834/G 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

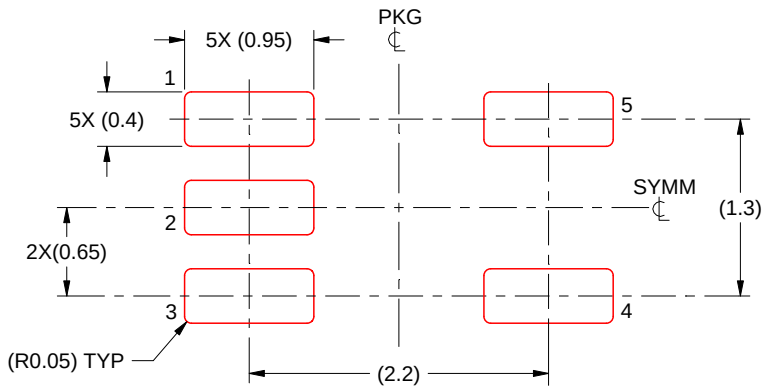


SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

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